



# STC2201

SamHop Microelectronics Corp.

Mar 15 2005 ver1.2

## P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (mΩ) Max
-20V	-2A	145 @ V <sub>GS</sub> = -4.5V
		195 @ V <sub>GS</sub> = -2.5V

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- SOT-323 package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Drain Current-Continuous <sup>a</sup> @ T <sub>c</sub> =25°C -Pulsed <sup>b</sup>	I <sub>D</sub>	-2	A
	I <sub>DM</sub>	-7	A
Drain-Source Diode Forward Current <sup>a</sup>	I <sub>S</sub>	-1	A
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	1.0	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	125	°C/W
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# STC2201

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V		1		uA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 10V, V <sub>DS</sub> = 0V		±100		nA
<b>ON CHARACTERISTICS<sup>b</sup></b>						
Gate Threshold Voltage	V <sub>G(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA	-0.5	-0.8	-1.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.0A		120	145	m-ohm
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -1.0A		170	195	m-ohm
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> = -5V, V <sub>GS</sub> = -4.5V	-5			A
Forward Transconductance	g <sub>Fs</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.0A		6		S
<b>DYNAMIC CHARACTERISTICS<sup>c</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1.0MHz		216		pF
Output Capacitance	C <sub>OSS</sub>			55		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			28		pF
<b>SWITCHING CHARACTERISTICS<sup>c</sup></b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = -10V, I <sub>D</sub> = -1A, V <sub>GS</sub> = -4.5V, R <sub>GEN</sub> = 6 ohm		12.7		ns
Rise Time	t <sub>r</sub>			15.4		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			25.7		ns
Fall Time	t <sub>f</sub>			20.4		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -2A, V <sub>GS</sub> = -4.5V		2.9		nC
Gate-Source Charge	Q <sub>gs</sub>			0.5		nC
Gate-Drain Charge	Q <sub>gd</sub>			1.1		nC

# STC2201

ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS <sup>b</sup>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = -1A$		-0.83	-1.2	V

Notes

- a. Surface Mounted on FR4 Board,  $t \leq 10\text{sec}$ .
- b. Pulse Test: Pulse Width  $\leq 300\text{us}$ , Duty Cycle  $\leq 2\%$ .
- c. Guaranteed by design, not subject to production testing.

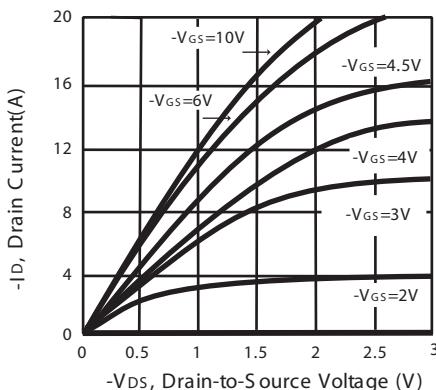


Figure 1. Output Characteristics

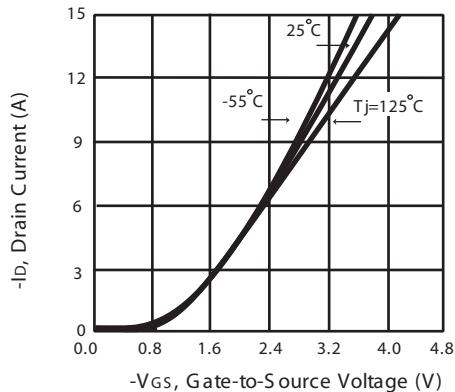


Figure 2. Transfer Characteristics

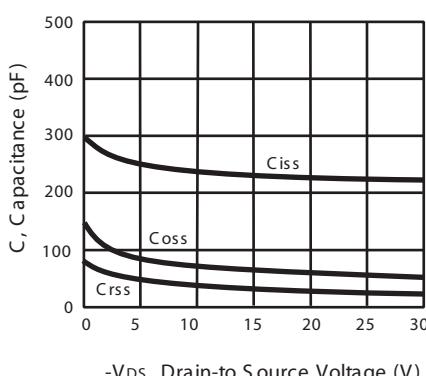


Figure 3. Capacitance

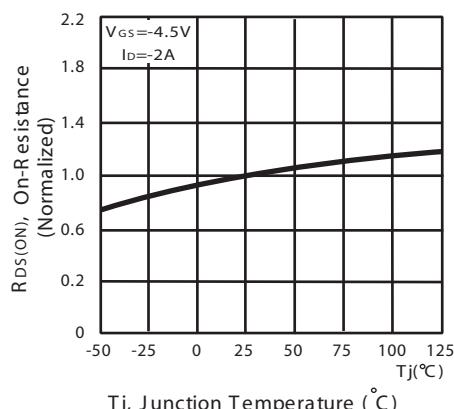
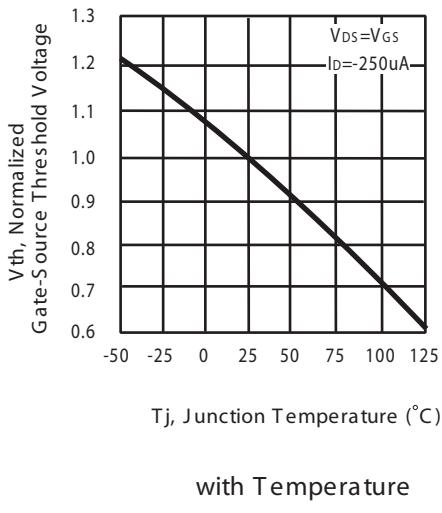
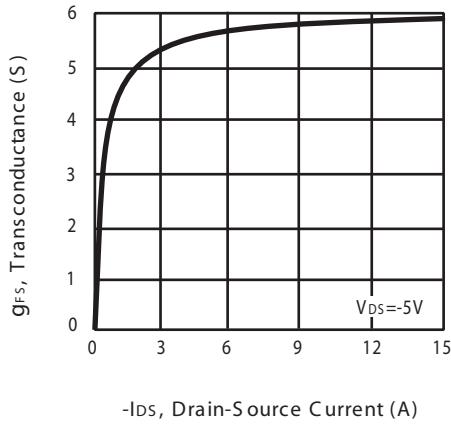


Figure 4. On-Resistance Variation with Temperature

# STC2201



with Temperature



- $I_{DS}$ , Drain-Source Current (A)

Figure 7. Transconductance Variation with Drain Current

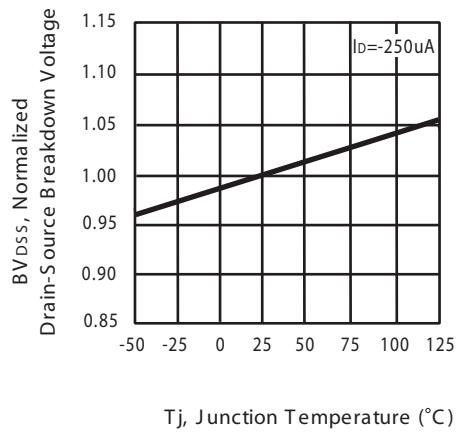
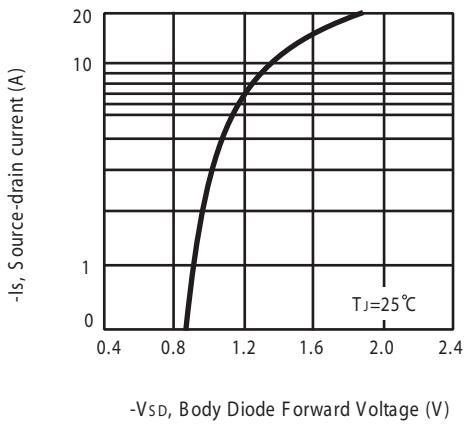
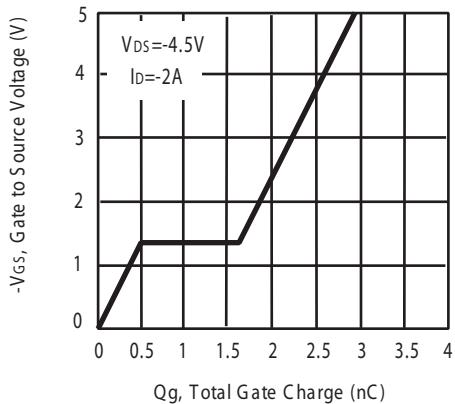


Figure 6. Breakdown Voltage Variation with Temperature



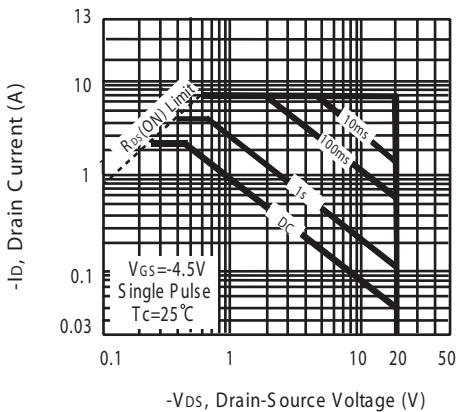
- $V_{SD}$ , Body Diode Forward Voltage (V)

Figure 8. Body Diode Forward Voltage Variation with Source Current



$Q_g$ , Total Gate Charge (nC)

Figure 9. Gate Charge



- $I_D$ , Drain Current (A)  
- $V_{DS}$ , Drain-Source Voltage (V)  
Figure 10. Maximum Safe Operating Area

# STC2201

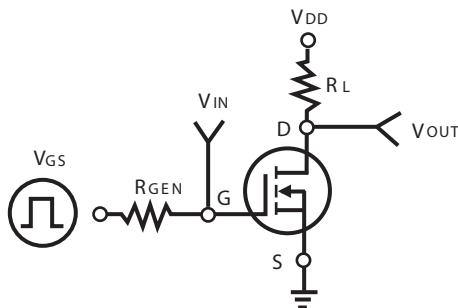


Figure 11. Switching Test Circuit

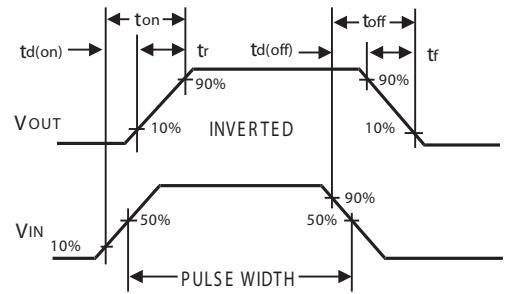
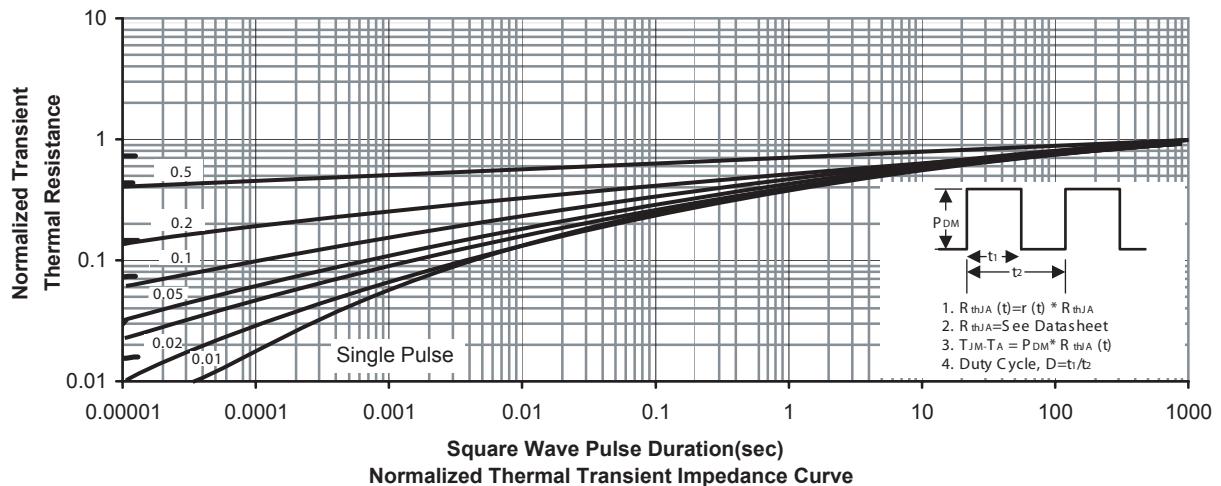


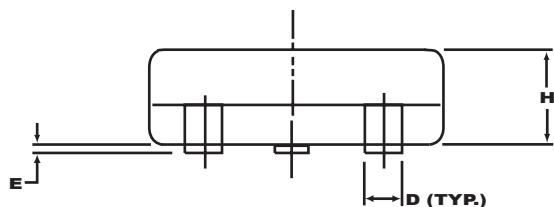
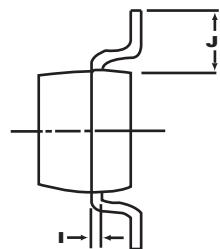
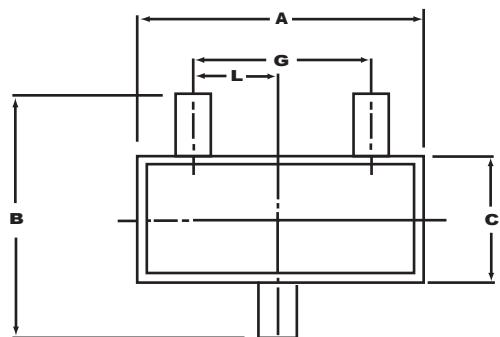
Figure 12. Switching Waveforms



# STC2201

## PACKAGE OUTLINE DIMENSIONS

SOT-323

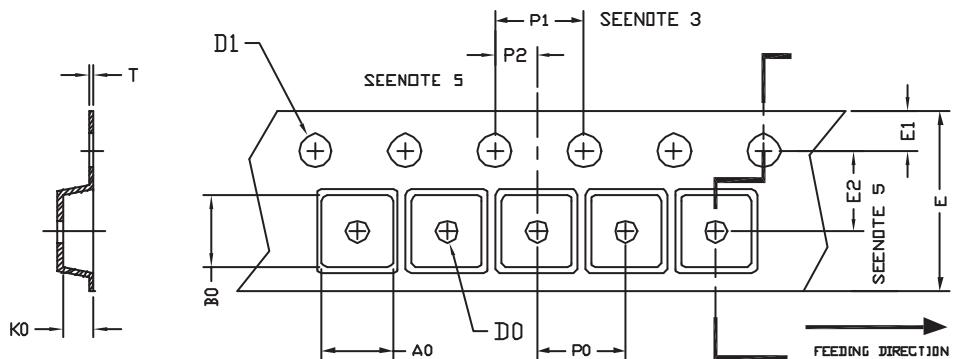


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.8	2.2	0.709	0.866
B	1.8	2.4	0.709	0.945
C	1.15	1.35	0.453	0.531
D	0.25	0.4	0.098	0.157
E	0	0.10	0	0.039
F	----	----	----	----
G	1.30 REF.		0.512 REF.	
H	0.80	1.00	0.315	0.394
I	0.10	0.25	0.039	0.098
J	----	---	----	----
L	0.65	----	0.256	----

# STC2201

## SOT-323 Tape and Reel Data

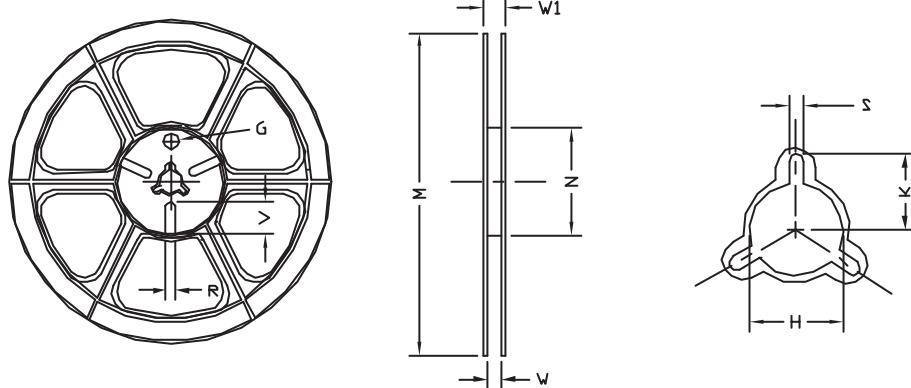
### SOT-323 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT-323	2.40 ±0.10	2.40 ±0.10	1.19 ±0.10	§ 1.00 +0.25	§ 1.50 +0.10	8.00 +0.30 -0.10	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.254 ±0.02

### SOT-323 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8mm	§ 178	§ 178 ±1	§ 60 ±1	9.00 ±0.5	12.00 ±0.5	§ 13.5 ±0.5	10.5	2.00 ±0.5	§ 10.0	5.00	18.00